/ Descriptions

TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

KSE340

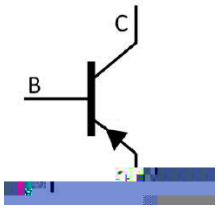
High collector-Emitter breakdown voltage Suitable for transformer complement to KSE340.

/ Applications

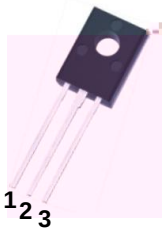
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High voltage general purpose applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

See Marking Instructions.

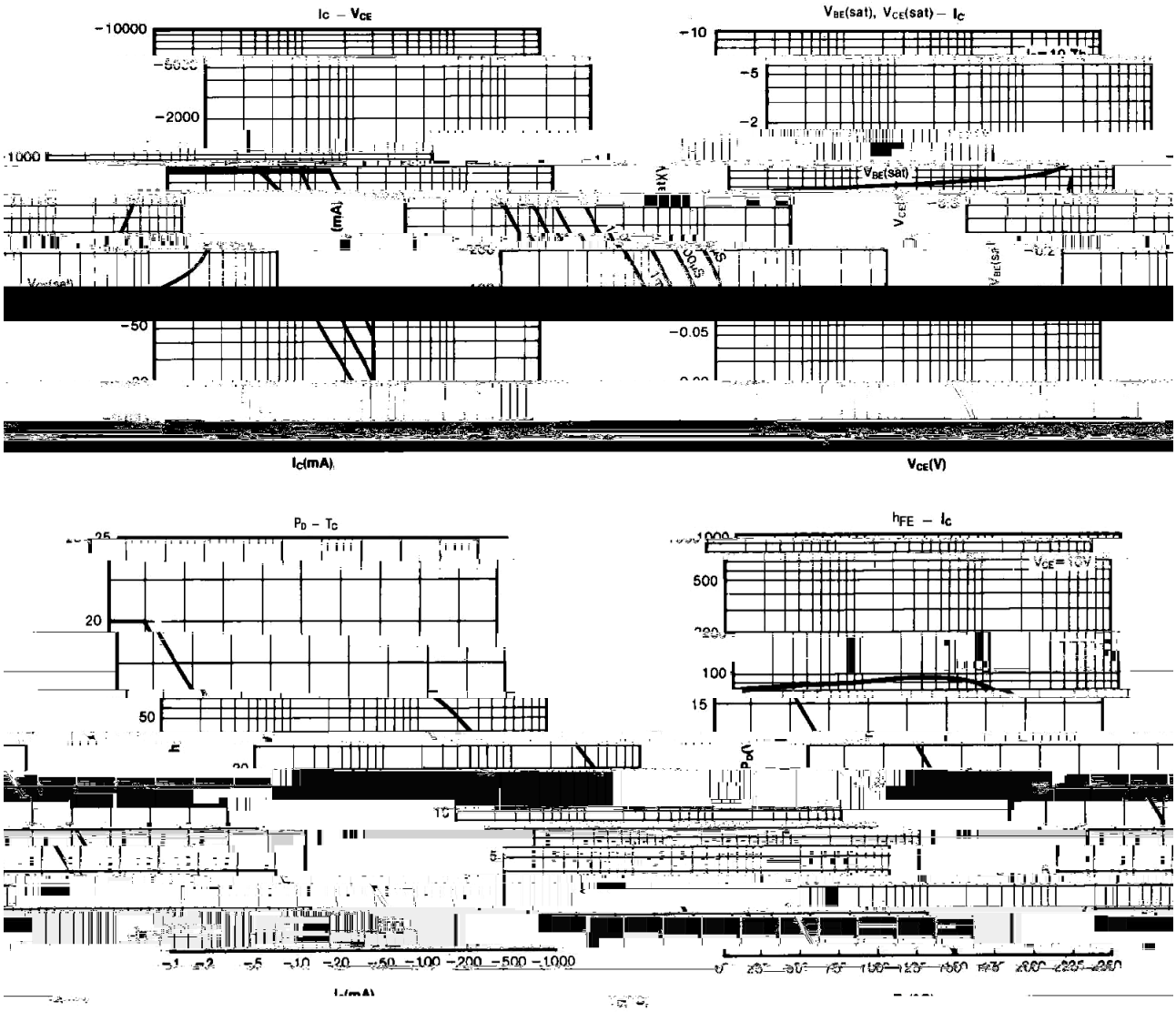
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current – Continuous	I_C	-500	mA
Collector Power Dissipation	P_C(Tc=25)	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

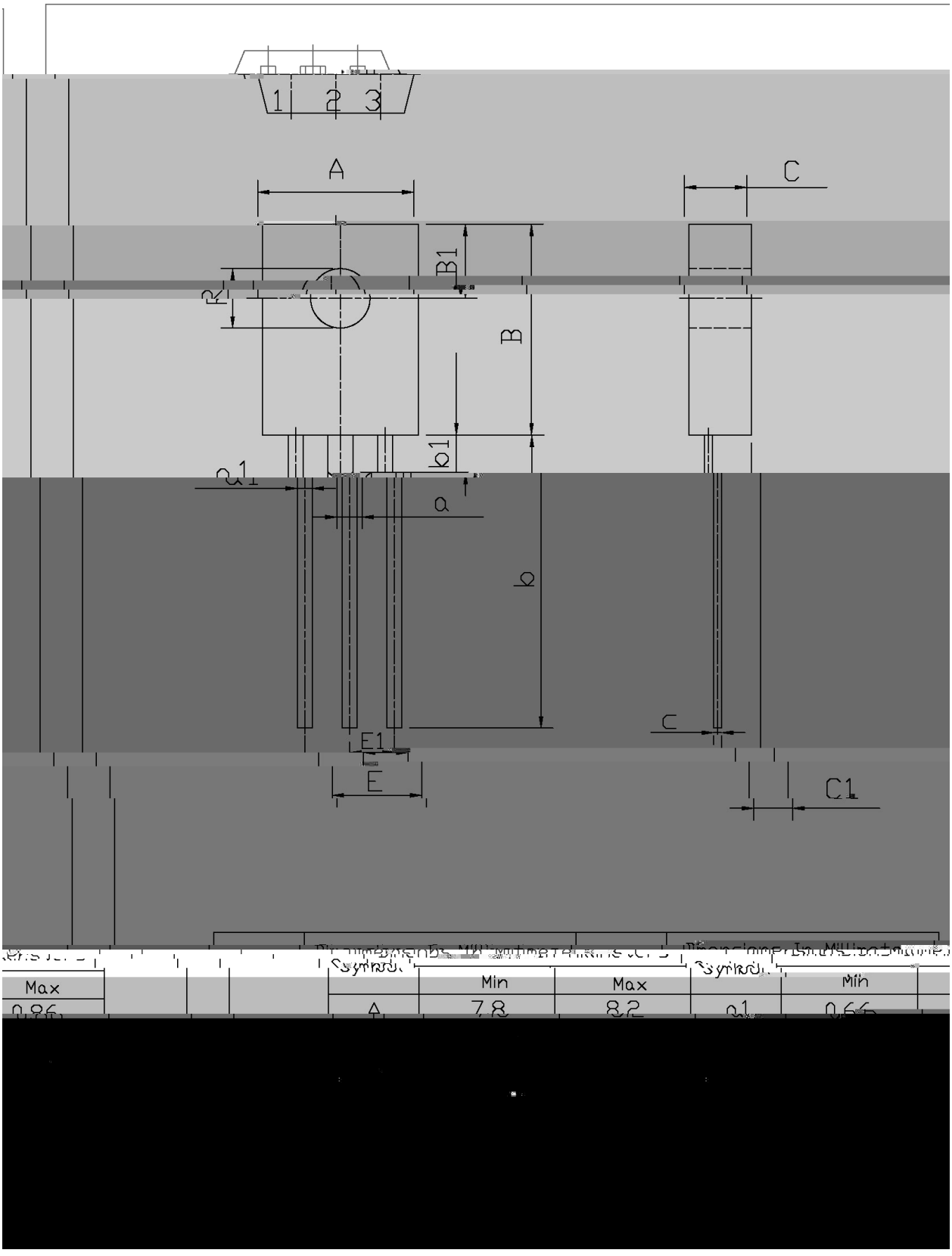
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-300			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-300V I_E=0			-100	μA
Emitter Cut-off Current	I_{EBO}	V_{BE}=-3.0V I_C=0			-100	μA
DC Current Gain	h_{FE}	V_{CE}=-10V I_C=-50mA	30		240	

/ Electrical Characteristic Curve



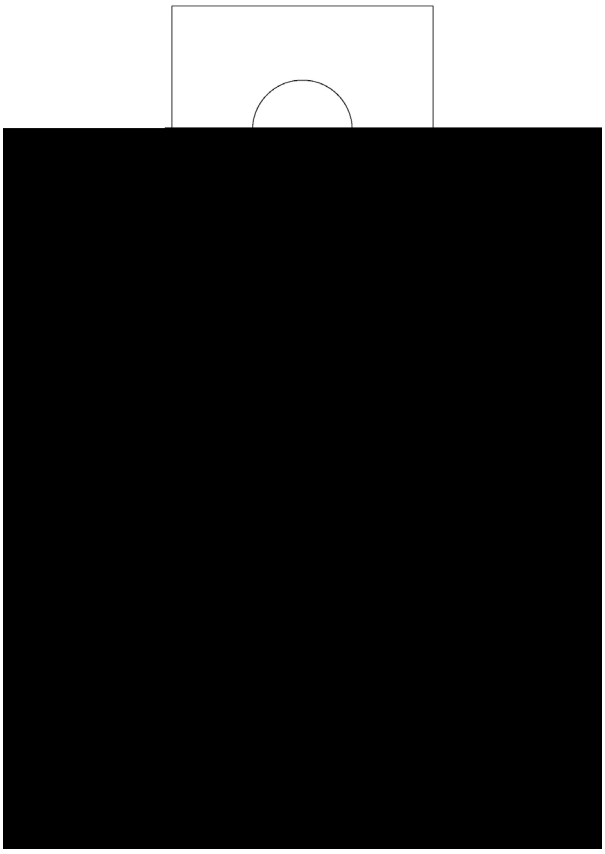
/ Package Dimensions

TO-126T 单位：mm



Symbol	Min	Max	Symbol	Min	Max
		0.86	A	7.8	8.2	a1	0.66	

/ Marking Instructions



BR

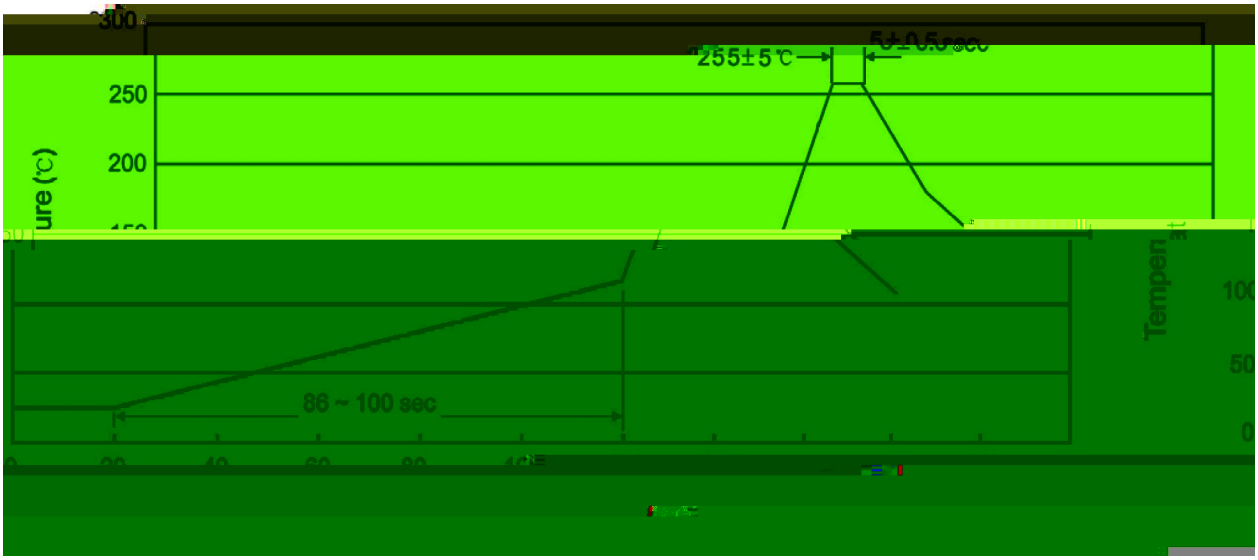
KSE350

****

Note:

BR:	Company Code
KSE350:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



				Note:
1	25 150		60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5		5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3		2 10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱